

Product Samples

ATP1001: Standard Metallization Bondable

Applied Thin-Film Products (ATP) is pleased to provide ceramic thin-film samples for your evaluation.

Standard TaN/TiW/Au metallization on Aluminum Oxide (Al_2O_3) is used in applications that require wire bonding, ribbon bonding, epoxy and various other types of attachment, such as Gold Tin, Gold Germanium and Gold Silicon.

ATP1001: Material is 15 mil As-Fired Al_2O_3
 TaN Resistors = 50 Ohms per Square
 TiW = 600–800 Ångströms
 Au = 120μ" minimum

Material Specifications

Asfired High Density 996 Aluminum Oxide Superstrate 996

Properties	Values
Chemical Composition	Al_2O_3
Purity	99.6%
Color	White
Nominal Density	3.88g/cm
Surface Finish (As-Fired)	3.0μ" (76.2nm)
Coefficient of Thermal Expansion (CTE)	$7.0 - 8.3 \times 10^{-6}$ (25–1000°C)
Camber	0.002" (0.508μm)
Thickness	0.015" (0.381mm)
Thickness Tolerance (±)	0.001" (25.4μm)
Thermal Conductivity 100°C	26.9 Watts/m ² K
Dielectric Constant 1 MHz	9.9 @ 1 MHz ±0.1
Dielectric Constant 10 GHz	9.7 @ 10 GHz ±0.1
Dissipation Factor (Loss Tangent)	0.0001 @ 1 MHz
Hardness (Rockwell)	87
Flexural Strength	90K (10 ⁻³) lbs/in ² (620Mpa)
Compressive Strength	54M (10 ⁻³) lbs/in ²
Grain Size	< 1.0μm

Material specifications provided by Coors Ceramic Company

Sample Provided



ATP offers build-to-print service for a wide range of materials and metallization schemes. ATP fabricates circuits on substrates from As-Fired Alumina to Beryllium Oxide to Fused Silica, even Silicon. Metallizations range from the standard Tan/TiW/Au to films including Nickel, Palladium, or Titanium.

At ATP, we constantly evolve our processing and material capabilities to reflect our customer's changing needs. If you have a circuit requirement that is out of the "normal" thin-film type, please contact ATP at 1.510.661.4287 or visit our website at www.thinfilm.com. ATP would enjoy discussing your application with you and working to develop a solution.